

1.3MHz 1.2A, Synchronous Step-Down Regulator

General Description

EML3412 is designed with high efficiency step down DC/DC converter for portable devices applications. It features with extreme low quiescent current with no load which is the best fit for extending battery life during the standby mode. The device operates from 2.5V to 5.5V input voltage and up to 1.2A output current capability. High 1.3MHz internal frequency makes small surface mount inductors and capacitors possible and reduces overall PCB board space. Further, build-in synchronous switch makes external Schottky diode is no longer needed and efficiency is improved. EML3412 is designed base on pulse width modulation (PWM) for low output voltage ripple and fixed frequency noise, low dropout mode provides 100% duty cycle operation. Low reference voltage is designed for achieving regulated output down to 0.6V. The device is available in an adjustable version. The EML3412 is available in TDFN-6 package.

Features

- Achieve 95% efficiency
- Input Voltage : 2.5V to 5.5V
- Output Current up to 1.2A
- Reference voltage 0.6V
- Quiescent Current 240μ A with No Switching
- Internal switching frequency 1.3MHz
- No Schottky Diode needed
- Low Dropout Operation: 100% Duty Cycle
- Shutdown current < 1μ A
- Excellent Line and Load Transient Response
- Over-current and Over-temperature Protection

Applications

- Blue-Tooth devices
- Cellular and Smart Phones
- Personal multi-media Player (PMP)
- Wireless networking
- Digital Still Cameras
- Portable applications

Typical Application (adjustable)

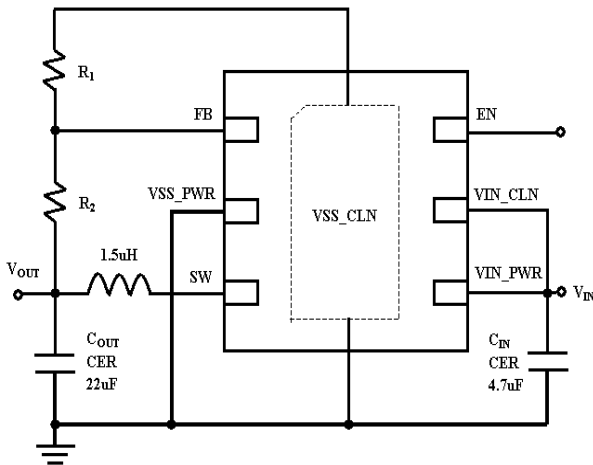


Fig. 1

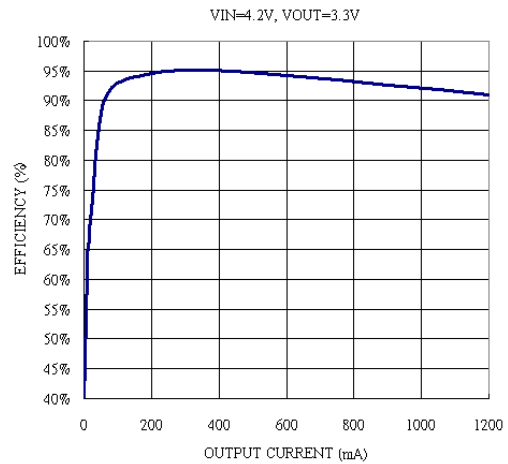
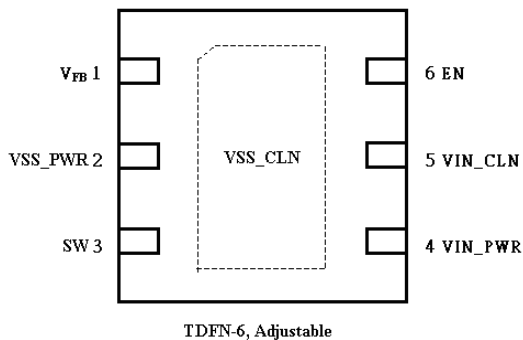


Fig. 2

Order, Mark & Packing Information

Package	Vout	Product ID	Marking	Packing
TDFN-6	00 (Adjustable)	EML3412-00FF06NRR		5K units Tape & Reel

Package configuration



EML3412-00FF06NRR
 00 Adjustable
 FF06 TDFN-6 Package
 NRR RoHS & Halogen free
 Rating: -40 to 85°C
 Package in Tape & Reel

Pin Functions

Pin #	Pin Name	Function
1	V _{FB} (Adjustable)	Feedback Pin. Receives the feedback voltage from an external resistive divider across the output.
	V _{out} (Fixed voltage)	Output Voltage Pin. An internal resistive divider divides the output voltage down for comparison to the internal reference voltage.
2	VSS_PWR	Power Ground Pin.
3	SW	Switch Pin. Must be connected to Inductor. This pin connects to the drains of the internal main and synchronous power MOSFET switches.
4	VIN_PWR	Power Input Pin. Must be closely decoupled to GND pin with a 4.7μF or greater ceramic capacitor.
5	VIN_CLN	Analog Input Pin. Must be closely decoupled to GND pin with a 4.7μF or greater ceramic capacitor.
6	EN	Enable Pin. Minimum 1.2V to enable the device. Maximum 0.4V to shut down the device. Do not leave this pin floating and enable the chip after Vin is in the input voltage range.
Exposed pad	VSS_CLN	Analog Ground Pin.

Absolute Maximum Ratings

Devices are subjected to failure if they stay above absolute maximum ratings.

Input Voltage -----	- 0.3V to 6V	Operating Temperature Range -----	-40°C to 85°C
EN, V _{FB} Voltages -----	- 0.3V to V _{IN}	Junction Temperature (Notes 1, 3) -----	125°C
SW Voltage -----	- 0.3V to (V _{IN} + 0.3V)	Storage Temperature Range -----	- 65°C to 150°C
PMOS Switch Source Current (DC) -----	2A	Lead Temperature (Soldering, 10 sec) -----	240°C
NMOS Switch Sink Current (DC) -----	2A	ESD Susceptibility HBM -----	2KV
Peak Switch Sink and Source Current -----	3.5A	MM -----	200V

Thermal data

Thermal resistance	Parameter	Value
θ_{JA}	Junction-ambient (Note.4)	55°C/W
θ_{JC}	Junction-case (Note.5)	10°C/W

Electrical Characteristics

The ● denotes specifications which apply over the full operating temperature range, otherwise specifications are T_A = 25°C. V_{IN} = 5V unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
I _{VFB}	Feedback Current				±100	nA	
V _{FB}	Regulated Feedback Voltage	T _A = 25°C	0.588	0.6	0.612	V	
		-40°C ≤ T _A ≤ 85°C	● 0.585	0.6	0.615		
V _{OUT} %	Output Voltage Accuracy		● -3		3	%	
Δ V _{FB}	Reference Voltage Line Regulation	V _{IN} = 2.5V to 5.5V	●		0.4	%/V	
Δ V _{OVL}	Output Over-voltage Lockout	Δ V _{OVL} = V _{OVL} - V _{FB}		20	50	80	mV
Δ V _{OUT}	Output Voltage Line Regulation	V _{IN} = 2.5V to 5.5V	●		0.4	%/V	
I _{PK}	Peak Inductor Current	V _{IN} = 3V, V _{FB} = 0.5V or V _{OUT} = 90%			2.4	A	
V _{LOADREG}	Output Voltage Load Regulation	I _{OUT} = 10mA to 1.2A			0.2	%/A	
I _S	Quiescent Current (Note 2)	V _{FB} = 0.5V or V _{OUT} = 90%			240	340	μ A
	Shutdown	V _{EN} = 0V, V _{IN} = 4.2V			0.1	1	μ A
f _{OSC}	Oscillator Frequency	V _{FB} = 0.6V or V _{OUT} = 100%	● 1.04	1.30	1.56	MHz	
R _{PFET}	R _{DS(ON)} of PMOS	I _{SW} = 750mA			0.18	Ω	
R _{NFET}	R _{DS(ON)} of NMOS	I _{SW} = -750mA			0.16	Ω	
I _{LSW}	SW Leakage	V _{EN} = 0V, V _{SW} = 0V or 5V, V _{IN} = 5V				±1	μ A
V _{EN}	Enable Threshold		● 1.2			V	
	Shutdown Threshold		●		0.4	V	
I _{EN}	EN Leakage Current		●			±1	μ A

Note 1: T_J is a function of the ambient temperature T_A and power dissipation P_D (T_J = T_A + (P_D)(55°C/W))

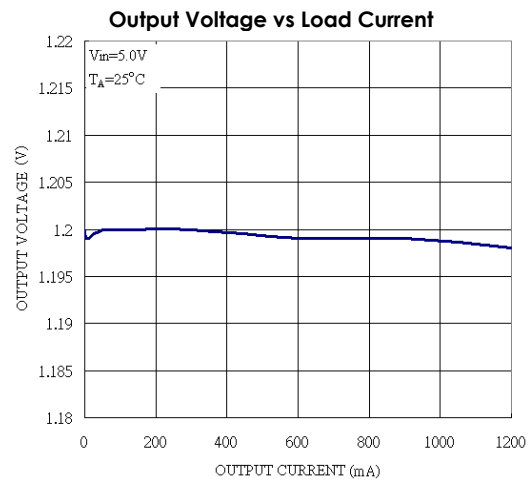
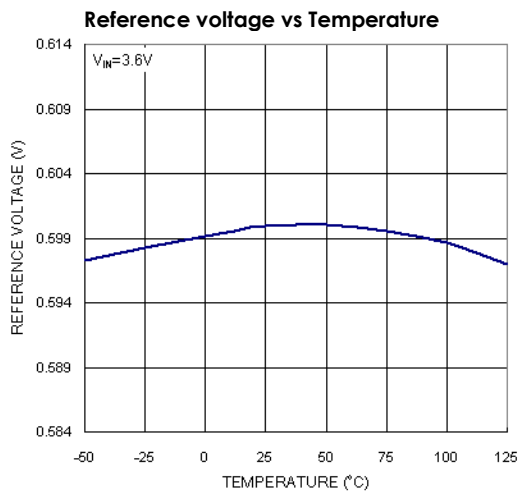
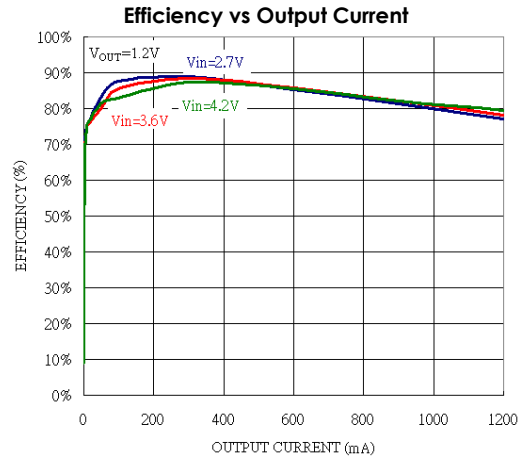
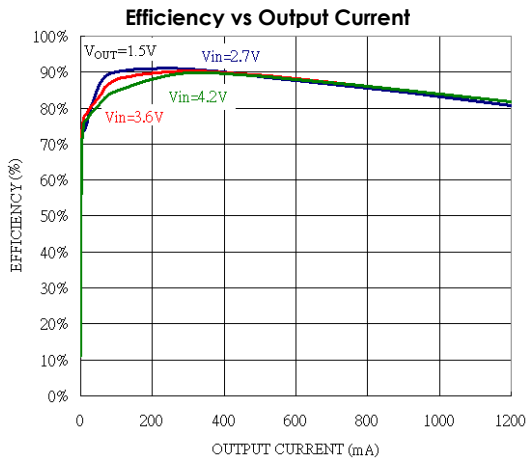
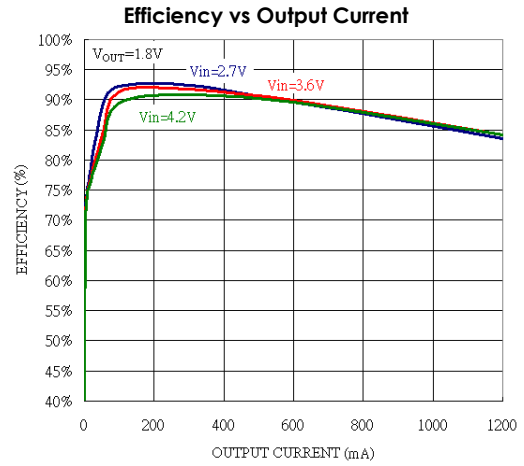
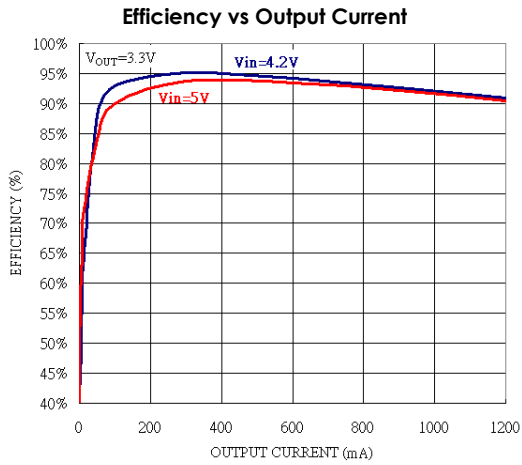
Note 2: Dynamic quiescent current is higher due to the gate charge being delivered at the switching frequency.

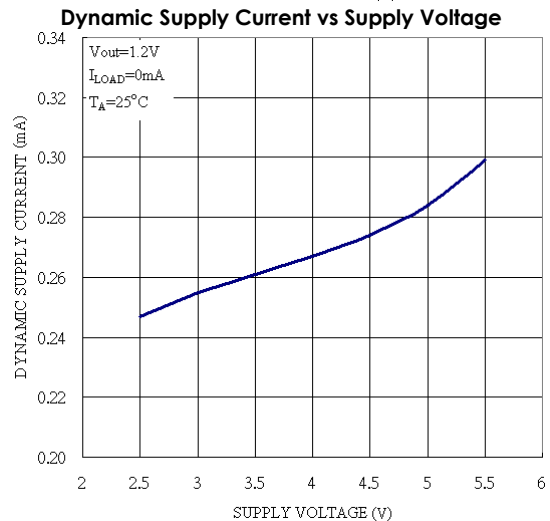
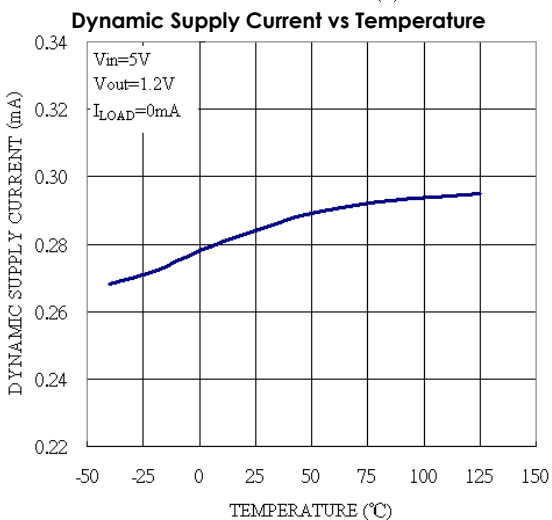
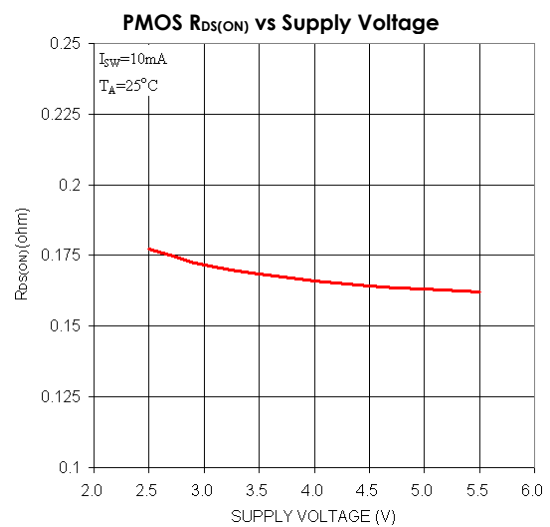
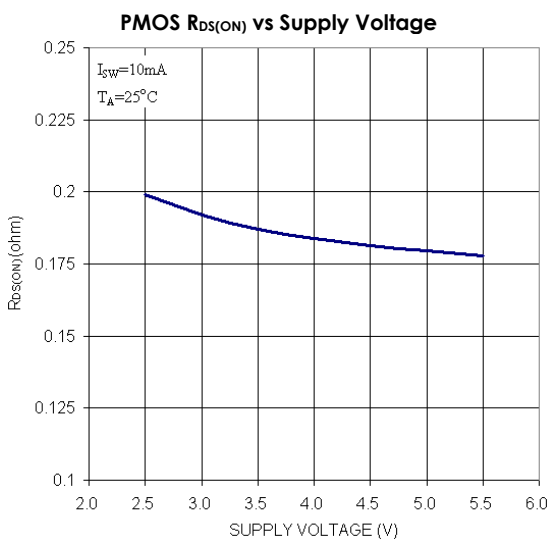
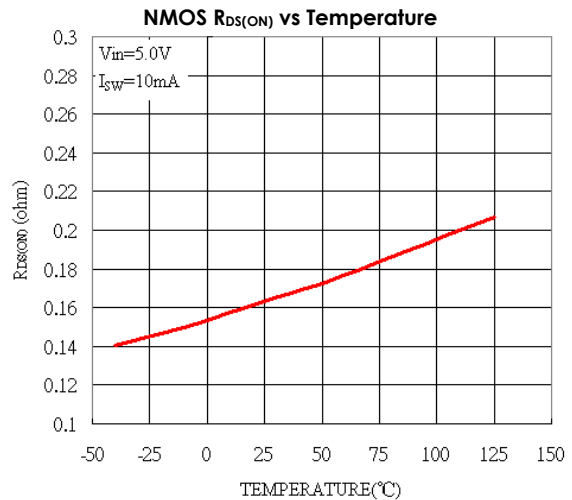
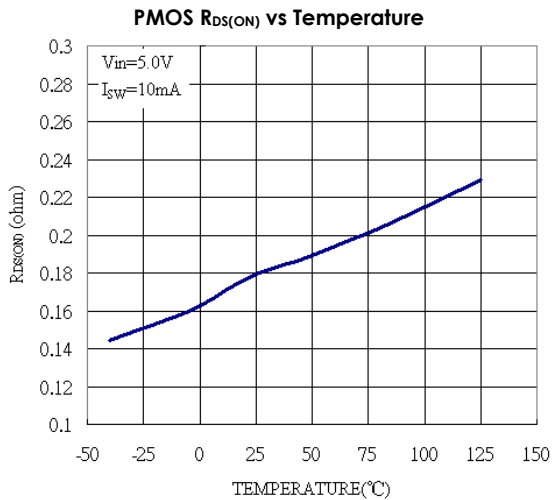
Note 3: This IC is build-in over-temperature protection to avoid damage from overload conditions.

Note 4: θ_{JA} is measured in the natural convection at T_A=25°C on a highly effective thermal conductivity test board (4 layers, 2S2P) according to the JEDEC 51-5 thermal measurement standard.

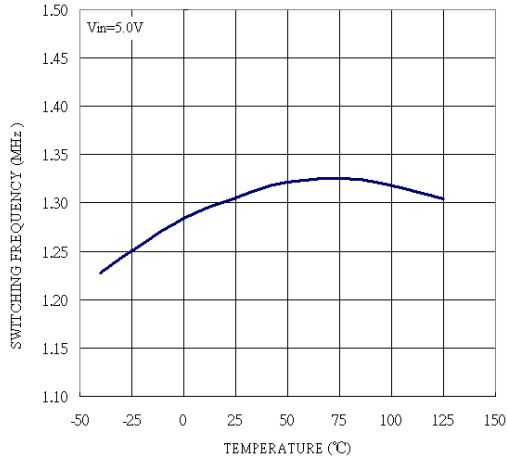
Note 5: θ_{JC} represents the heat resistance between the chip and the package top case.

Typical Performance Characteristics

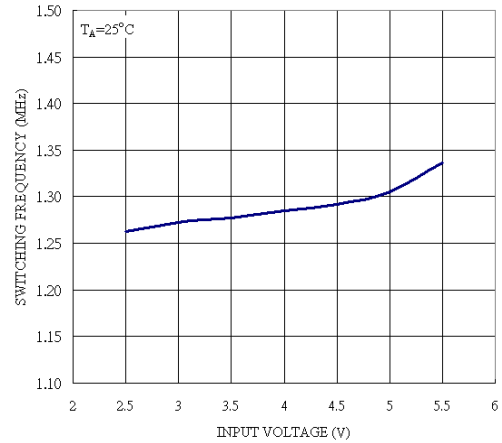




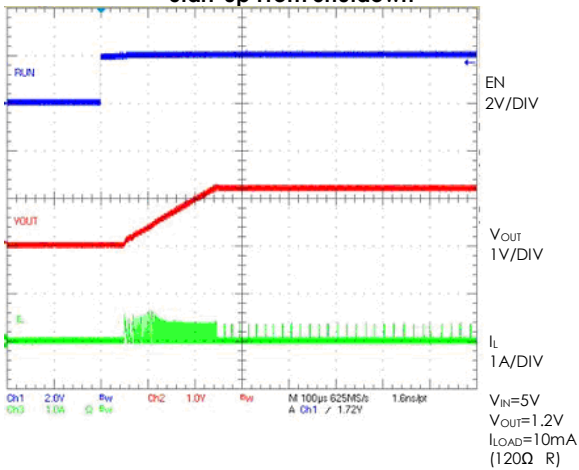
Switching Frequency vs Temperature



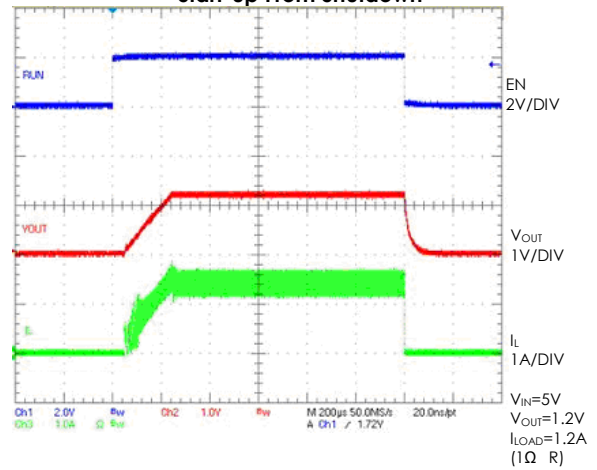
Switching Frequency vs Supply Voltage



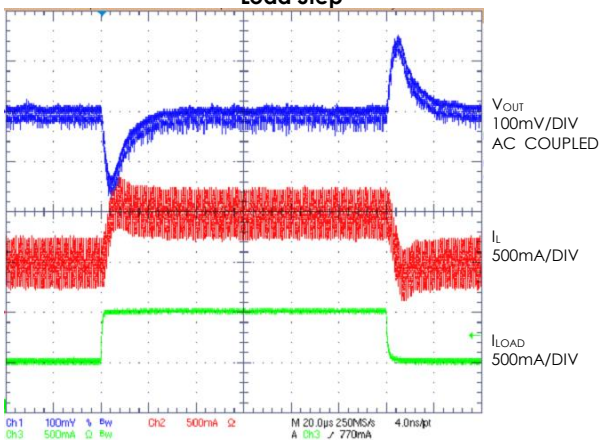
Start-up From Shutdown



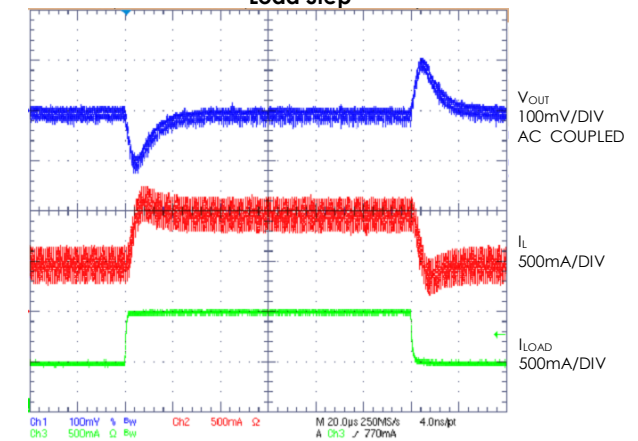
Start-up From Shutdown



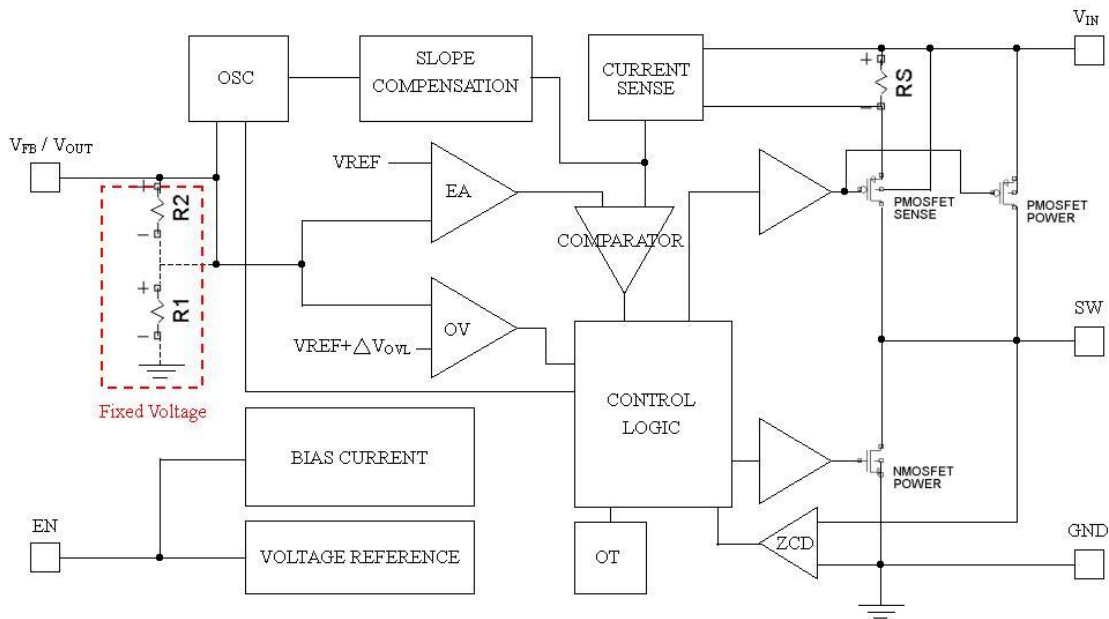
Load Step



Load Step



Functional Block Diagram



Applications

Inductor Selection

Basically, inductor ripple current and core saturation current are two factors considered to decide the inductor value.

$$\Delta I_L = \frac{1}{f \cdot L} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right) \quad \text{Eq. 1}$$

The Eq. 1 shows the inductor ripple current is a function of frequency, inductance, V_{IN} and V_{OUT} . It is recommended to set ripple current to 40% of max. load current. A low ESR inductor is preferred.

C_{IN} and C_{OUT} Selection

A low ESR input capacitor can prevent large voltage transients at V_{IN} . The RMS current of input capacitor is required larger than I_{RMS} calculated by:

$$I_{RMS} \cong I_{OMAX} \frac{\sqrt{V_{OUT}(V_{IN} - V_{OUT})}}{V_{IN}} \quad \text{Eq. 2}$$

ESR is an important parameter to select C_{OUT} . The output ripple V_{OUT} is determined by:

$$\Delta V_{OUT} \cong \Delta I_L \left(ESR + \frac{1}{8 \cdot f \cdot C_{OUT}} \right) \quad \text{Eq. 3}$$

Higher values, lower cost ceramic capacitors are now available in smaller sizes. These ceramic capacitors have high ripple currents, high voltage ratings and low ESR that make them ideal for switching regulator applications. Optimize very low output ripple and small circuit size is doable from C_{OUT} selection since C_{OUT} does not affect the internal control loop stability. It is recommended to use the X5R or X7R which have the best temperature and voltage characteristics of all the ceramics for a given value and size.

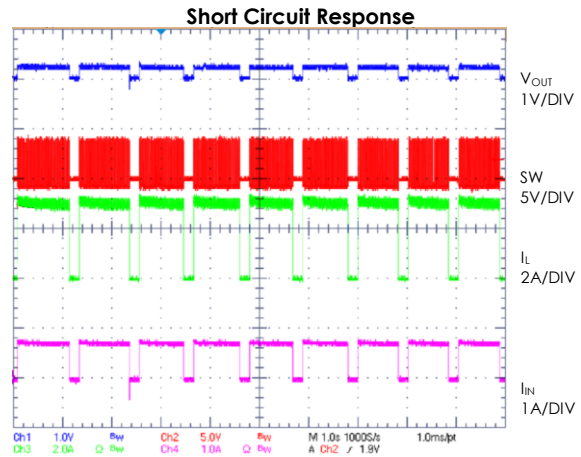
Output Voltage

In the adjustable version, the output voltage can be determined by:

$$V_{OUT} = 0.6V \left(1 + \frac{R_2}{R_1} \right) \quad \text{Eq. 4}$$

Short Circuit Behavior

EML3412 has over-current and over-temperature protection. Over-current protection cycle by cycle limits P-driver FET current to prevent inductor current from losing control. Over-temperature protection function turns off driver FETs when junction temperature is high and recovers to normal operation after it is cool enough. When EML3412 is used to transfer $V_{IN}=5V$ to $V_{OUT}=1.2V$, shorting V_{OUT} to ground makes over-current and over-temperature protection active. The waveform is shown as the following diagram.



Thermal Considerations

Although thermal shutdown is built-in in EML3412 that protect the device from thermal damage, the total power dissipation that EML3412 can sustain should be based on the package thermal capability. The formula to ensure the safe operation is shown in Note 1.

To avoid the EML3412 from exceeding the maximum junction temperature, the user will need to do some thermal analysis.

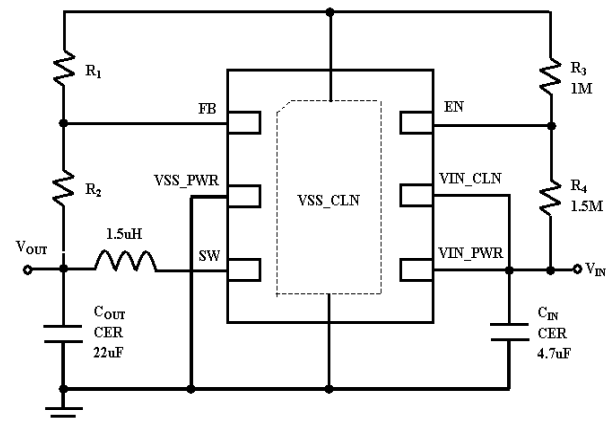
Guidelines for PCB Layout

To ensure proper operation of the EML3412, please note the following PCB layout guidelines:

1. The GND trace, the SW trace and the V_{IN} trace should be kept short, direct and wide.
2. V_{FB} pin must be connected directly to the feedback resistors. Resistive divider R_1/R_2 must be connected and parallel to the output capacitor C_{OUT} .
3. The input capacitor C_{IN} must be connected to pin V_{IN} as closely as possible.
4. Keep SW node away from the sensitive V_{FB} node since this node is with high frequency and voltage swing.
5. Keep the (-) plates of C_{IN} and C_{OUT} as close as possible.
6. Connect all analog grounds to a common node and connect the common node to power ground through an independent path.

Self-Enable Application

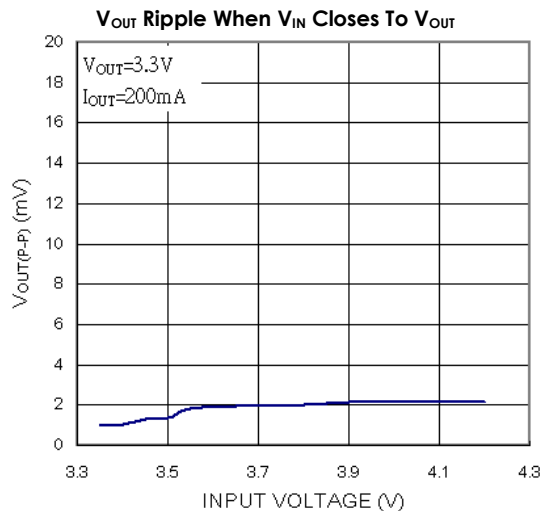
A self-enable function could be used when EML3412 is connected as the following diagram:



The resistor ratio R3:R4=1:1.5 is recommended.

Output Voltage Ripple When V_{IN} Closes To V_{OUT}

EML3412 goes into LDO mode when input voltage closes to output voltage. The transition from PWM mode to LDO mode is smooth. Bottom diagram shows the relationship of output voltage ripple versus input voltage when output voltage is 3.3V and EML3412 provides 200mA load current.



Design Example

Recommended Components

Supplier	Inductance (µH)	I _{sat} (A)	DCR _{max} (mΩ)	Dimensions (mm)	Part Number
Coilcraft	1.5	14	13	12.3 x 12.3 x 6	MSS1260-152NLB

Supplier	Capacitance (µF)	Package	Part Number
YAGEO	4.7	0805	CC0805KKX5R6BB475
TAIYO YUDEN	22	1812	EMK432BJ226KM-T

Assume the EML3412 is used in a single lithium-ion battery-powered application. The V_{IN} range will be about 2.7V to 4.2V. Output voltage is 1.8V.

With this information we can calculate L using equation:

$$L = \frac{1}{f \cdot \Delta I_L} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right)$$

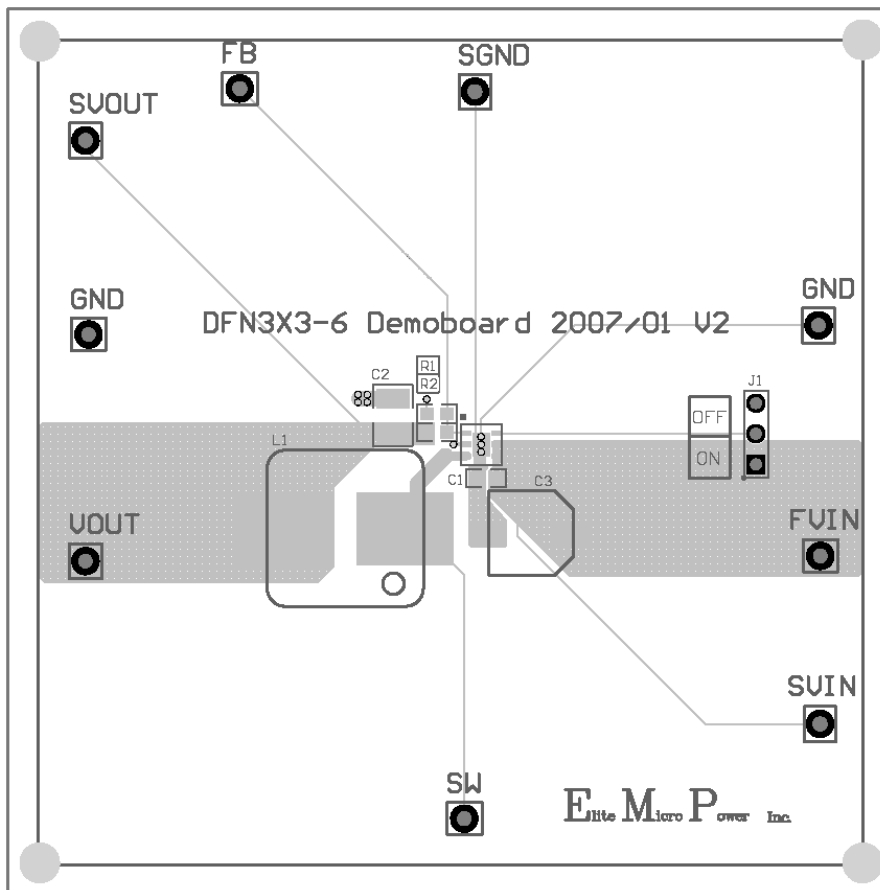
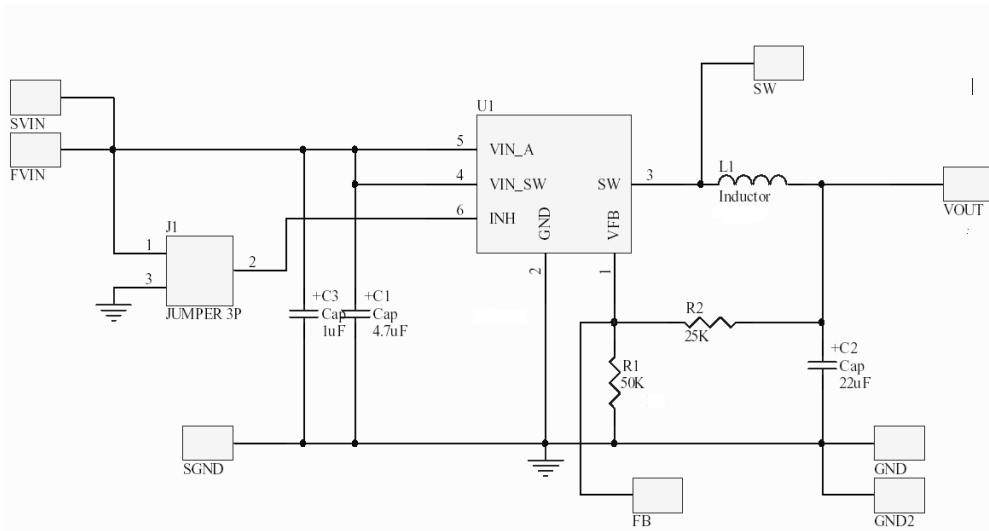
Substituting V_{OUT} = 1.8V, V_{IN} = 4.2V, ΔI_L = 480mA and f = 1.3MHz in eq. 1 gives:

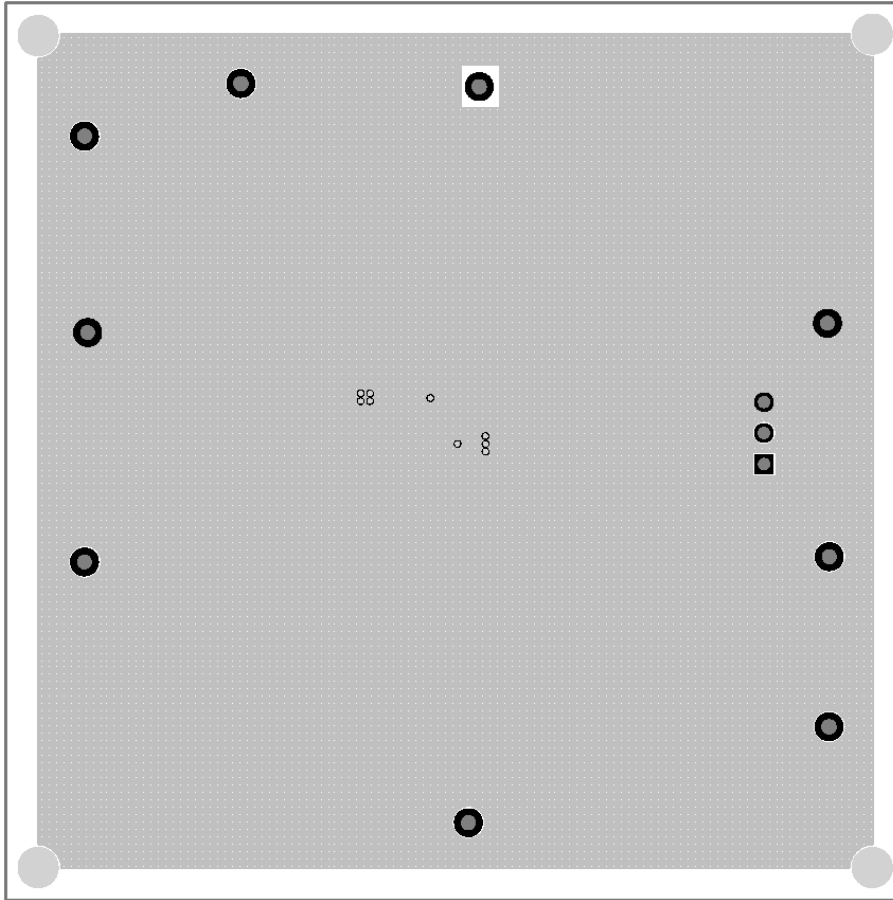
$$L = \frac{1.8V}{1.3MHz \cdot 480mA} \left(1 - \frac{1.8V}{4.2V} \right) = 1.65\mu H$$

A 1.5µH inductor could be chosen with this application. A greater inductor with less equivalent series resistance makes best efficiency. C_{IN} will require an RMS current rating of at least I_{LOAD(MAX)}/2 and low ESR. In most cases, a ceramic capacitor will satisfy this requirement.

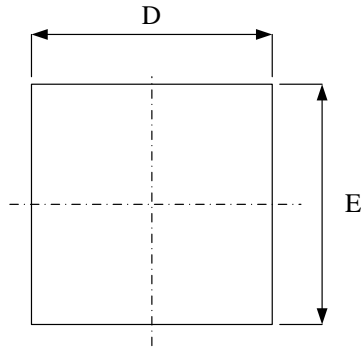
Application (Continued)

Typical schematic for PCB layout

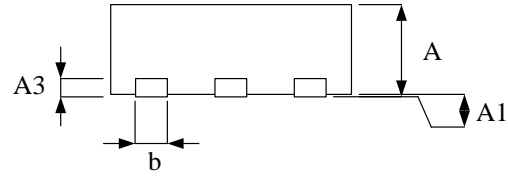




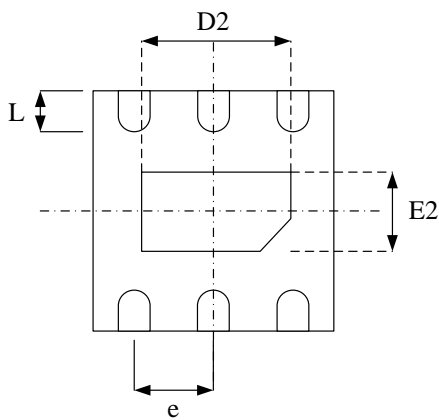
Package Outline Drawing TDFN-6L (3x3 mm)



TOP VIEW



SIDE VIEW



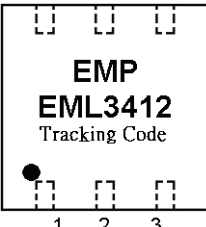
BOTTOM VIEW

Symbol	Dimension in mm	
	Min	Max
A	0.70	0.85
A1	0.00	0.05
A3	0.18	0.25
b	0.25	0.45
D	2.95	3.05
E	2.95	3.05
e	0.95 BSC	
L	0.20	0.50

Exposed pad

	Dimension in mm	
	Min	Max
D2	2.20	2.60
E2	1.40	1.75

Old Order, Marking & Packing Information

Package	Vout	Product ID	Marking	Packing
TDFN-6	00 (Adjustable)	EML3412-00FF06NRR	 <p>6 5 4</p> <p>EMP EML3412 Tracking Code</p> <p>1 2 3</p> <p>PIN1 DOT</p>	5K units Tape & Reel

Revision History

Revision	Date	Description
2.0	2009.06.05	EMP transferred from version 1.2
2.1	2010.06.02	To revise circuitry
2.2	2010.09.30	Package dimension update
2.3	2011.01.28	Revise electrical characteristics(VEN)
2.4	2013.02.18	1. Added the note4 and note5 in the electrical characteristics 2. Update the TDFN-6L package outline
2.5	2013.10.24	Modify marking

Important Notice

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